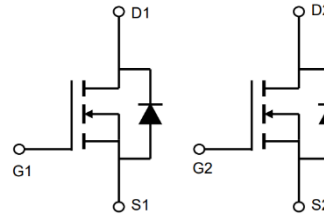


60V N-Channel Enhancement Mode MOSFET

Description

The AP70H06NF uses advanced **APM-SGT_r** technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = 60V$ $I_D = 70A$

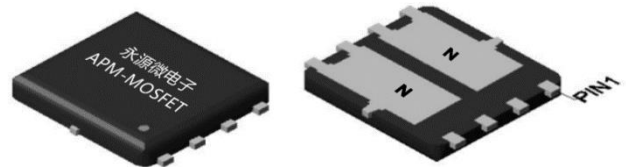
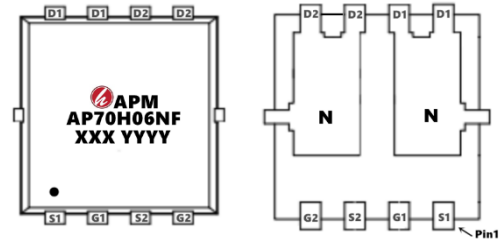
$R_{DS(ON)} < 10m\Omega$ @ $V_{GS}=10V$ (Type: **7.5m Ω**)

Application

Battery protection

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP70H06NF	PDFN5*6-8L	AP70H06NF XXX YYYY	5000

Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Value	Unit
V _{DS}	Drain source voltage	60	V
V _{GS}	Gate source voltage	±20	V
$I_D@T_A=25^\circ C$	Continuous drain current	70	A
$I_D@T_A=70^\circ C$	Continuous drain current	45	A
IDM	Pulsed drain current	280	A
$P_D@T_A=25^\circ C$	Power dissipation	60	W
EAS	Single pulsed avalanche energy	30	mJ
TSTG	Storage Temperature Range	-55 to 150	°C
T _j	Operation and storage temperature	-55 to 150	°C
R θ JC	Thermal resistance, junction-case	2.1	°C/W
R θ JA	Thermal resistance, junction-ambient5)	25	°C/W



60V N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
BVDSS	Drain-source breakdown voltage	V _{GS} =0 V, I _D =250 μA	60	68		V
VGS(th)	Gate threshold voltage	V _{DS} =V _{GS} , I _D =250 μA	1.2	1.5	2.5	V
RDS(ON)	Drain-source on-state resistance	V _{GS} =10 V, I _D =20 A		7.5	10	mΩ
RDS(ON)	Drain-source on-state resistance	V _{GS} =4.5 V, I _D =10 A		10	13	mΩ
IGSS	Gate-source leakage current	V _{GS} =±20 V			±100	nA
IDSS	Drain-source leakage current	V _{DS} =60 V, V _{GS} =0 V			1	μA
Ciss	Input capacitance	V _{GS} =0 V, V _{DS} =50 V, f=100 kHz		1182.1		pF
Coss	Output capacitance			199.5		pF
Crss	Reverse transfer capacitance			4.1		pF
td(on)	Turn-on delay time	V _{GS} =10 V, V _{DS} =50 V, R _G =2 Ω, I _D =10 A		17.9		ns
t _r	Rise time			4.0		ns
td(off)	Turn-off delay time			34.9		ns
t _f	Fall time			5.5		ns
Q _g	Total gate charge	I _D =10 A, V _{DS} =50 V, V _{GS} =10 V		18.4		nC
Q _{gs}	Gate-source charge			3.3		nC
Q _{gd}	Gate-drain charge			3.1		nC
V _{plateau}	Gate plateau voltage			2.8		V
I _S	Diode forward current	V _{GS} <V _{th}			60	A
ISP	Pulsed source current				180	
VSD	Diode forward voltage	I _S =20 A, V _{GS} =0 V			1.3	V
trr	Reverse recovery time	I _S =10 A, di/dt=100 A/μs		41.8		ns
Q _{rr}	Reverse recovery charge				36.1	nC
I _{rrm}	Peak reverse recovery current				1.4	A

Note

- 1、 Calculated continuous current based on maximum allowable junction temperature.
- 2、 Repetitive rating; pulse width limited by max. junction temperature.
- 3、 Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4、 V_{DD}=50 V, R_G=50 Ω, L=0.3 mH, starting T_J=25 °C.
- 5、 The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.

60V N-Channel Enhancement Mode MOSFET

Typical Characteristics

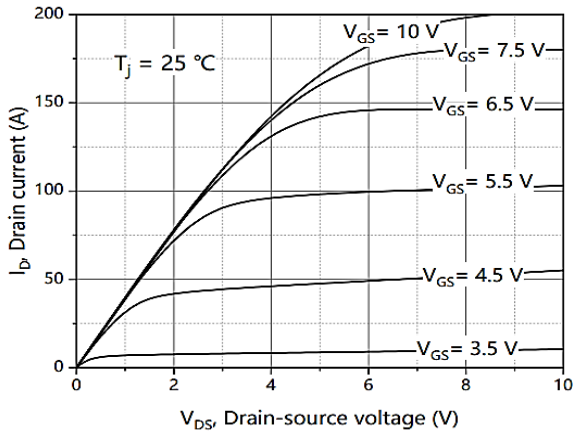


Figure 1. Typ. output characteristics

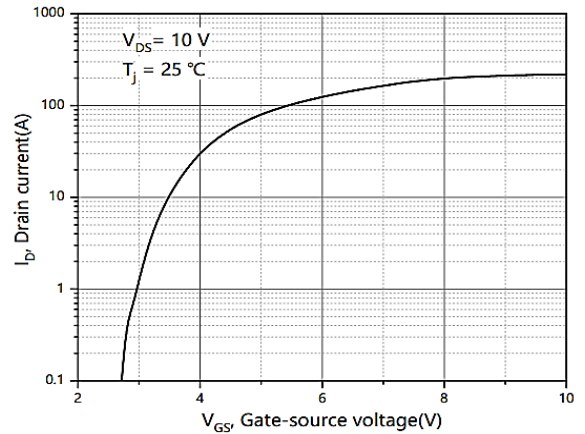


Figure 2. Typ. transfer characteristics

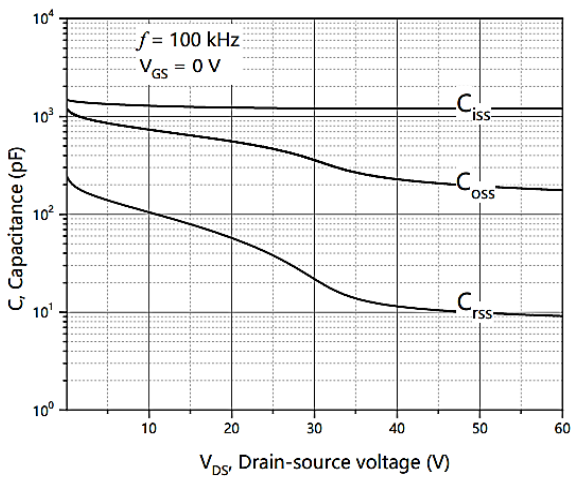


Figure 3. Typ. capacitances

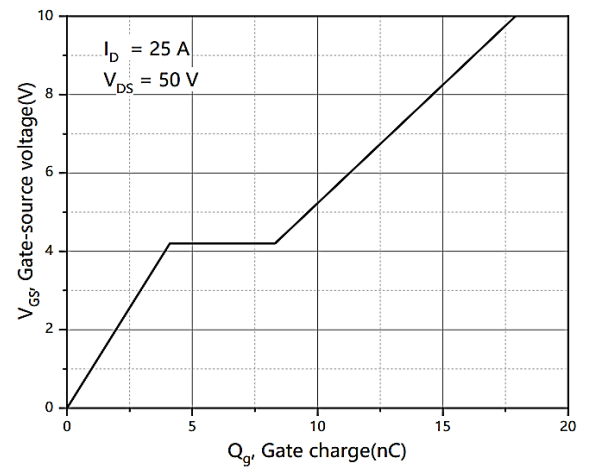


Figure 4. Typ. gate charge

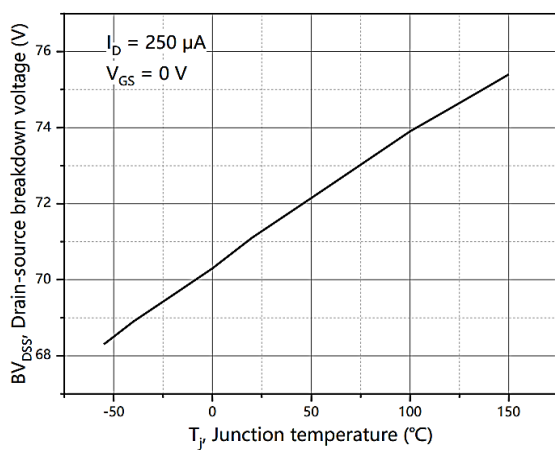


Figure 5. Drain-source breakdown voltage

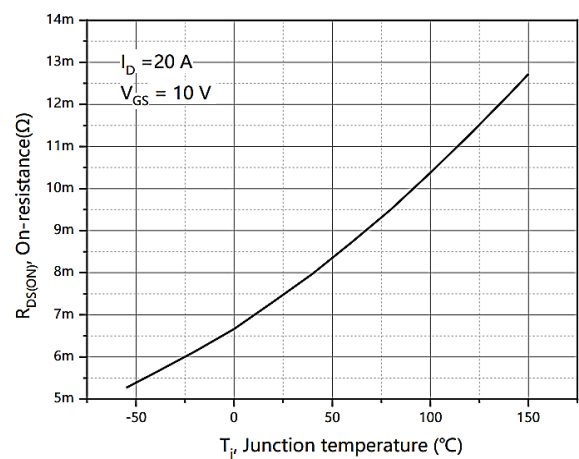


Figure 6. Drain-source on-state resistance

60V N-Channel Enhancement Mode MOSFET

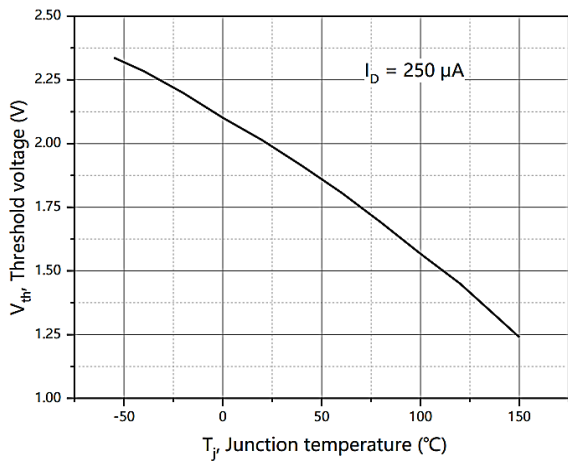


Figure 7. Threshold voltage

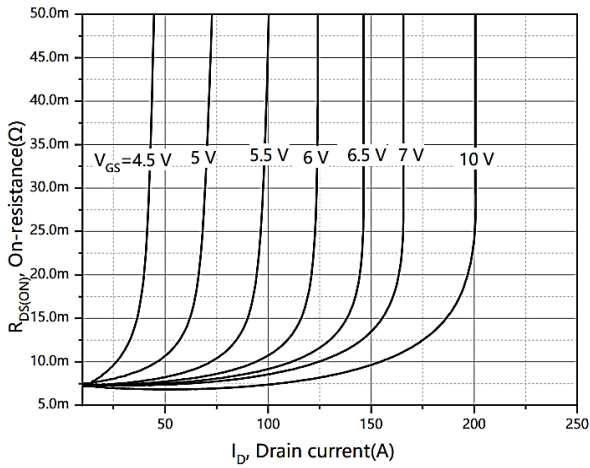


Figure 9. Drain-source on-state resistance

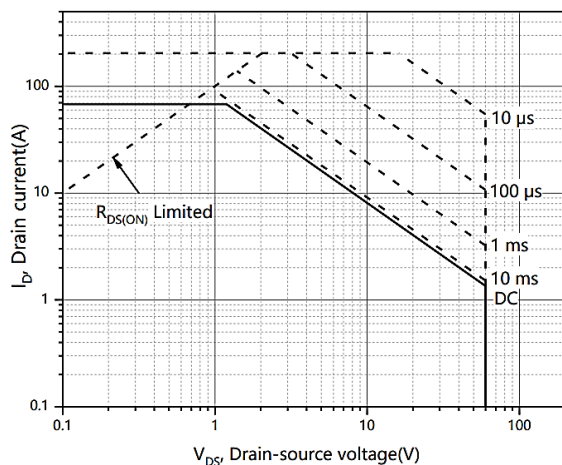


Figure 11. Safe operation area $T_C=25\text{ }^\circ\text{C}$

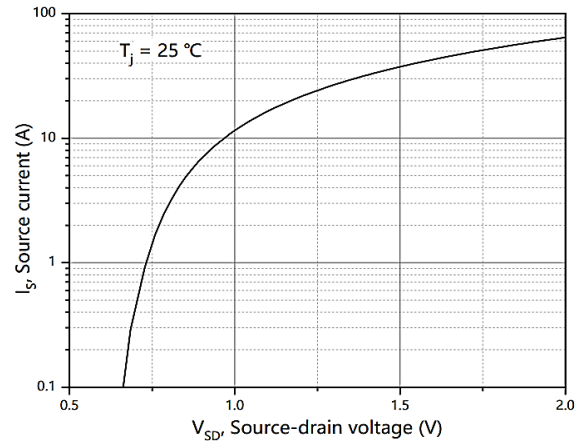


Figure 8. Forward characteristic of body diode

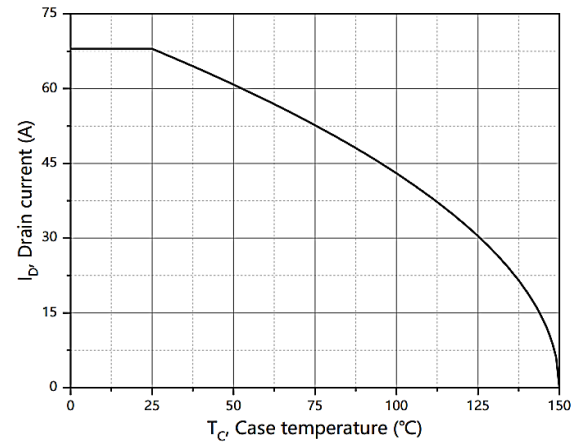


Figure 10. Drain current

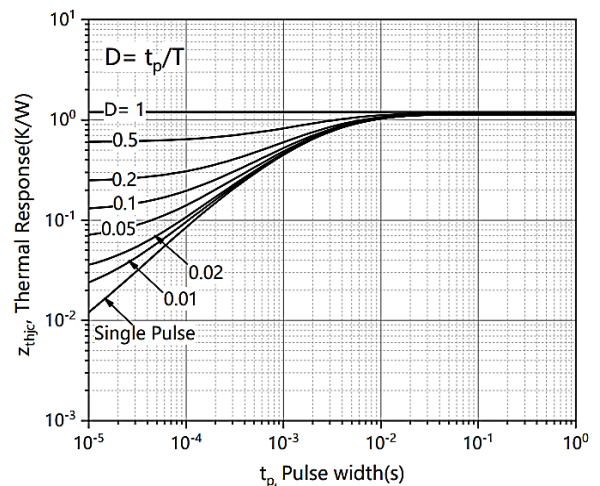
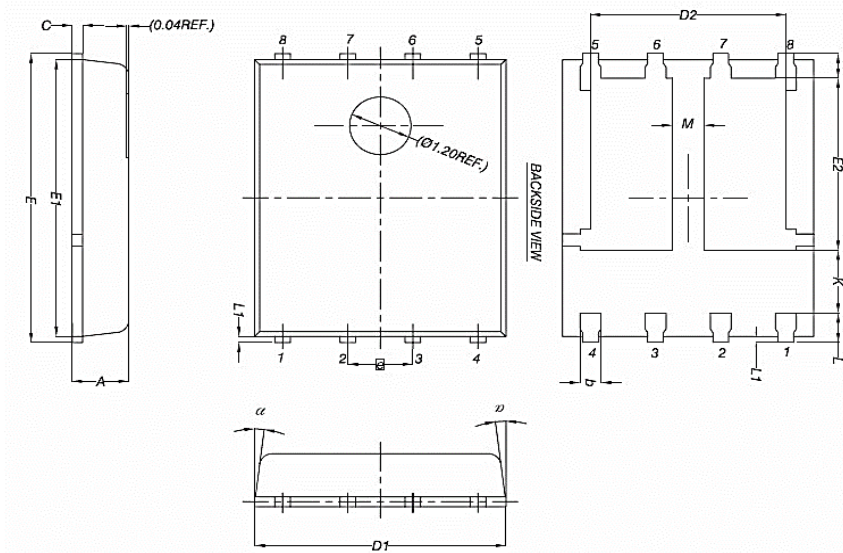


Figure 12. Max. transient thermal impedance

60V N-Channel Enhancement Mode MOSFET Package Mechanical Data-DFN5*6-8L-JQ Double



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	3.30	3.45
E2	3.38	3.05	3.20
e	1.27BSC		
H	0.41	0.51	0.61
K	1.10	--	--
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	--	--
a	0°	--	12°

60V N-Channel Enhancement Mode MOSFET**Attention**

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AP70H06NF

60V N-Channel Enhancement Mode MOSFET

Edition	Date	Change
Rve1.0	2019/8/1	Initial release

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